

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- Direct interfacing to logic level ICs
- · Direct interfacing to low power gate drivers and microcontrollers
- Medium blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

## 3. Applications

- AC Fan controller
- General purpose low power phase control
- General purpose low power switching

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	400	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4; Fig. 5}$	-	-	9	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 107 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	0.8	A
Static charac	cteristics			·		
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1	5	mA
		$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; Fig. 9	-	2	5	mA





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#### 4Q Triac

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ T <sub>j</sub> = 25 °C; Fig. 9	-	2	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	4	7	mA

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2
2	T2	main terminal 2		sym051
3	G	gate		
4	T2	main terminal 2	☐1 ☐2 ☐3 SC-73 (SOT223)	

# 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BT1308W-400D	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

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## 7. Limiting values

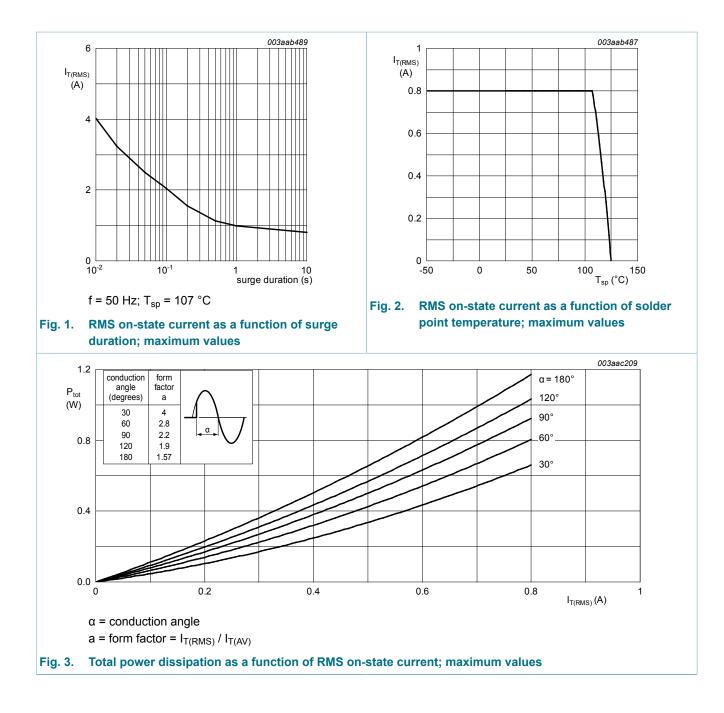
#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	400	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>sp</sub> ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	0.8	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	9	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	10	A
l <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.32	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/µs; T2+ G+	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/µs; T2+ G-	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/µs; T2- G-	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/µs; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	1	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

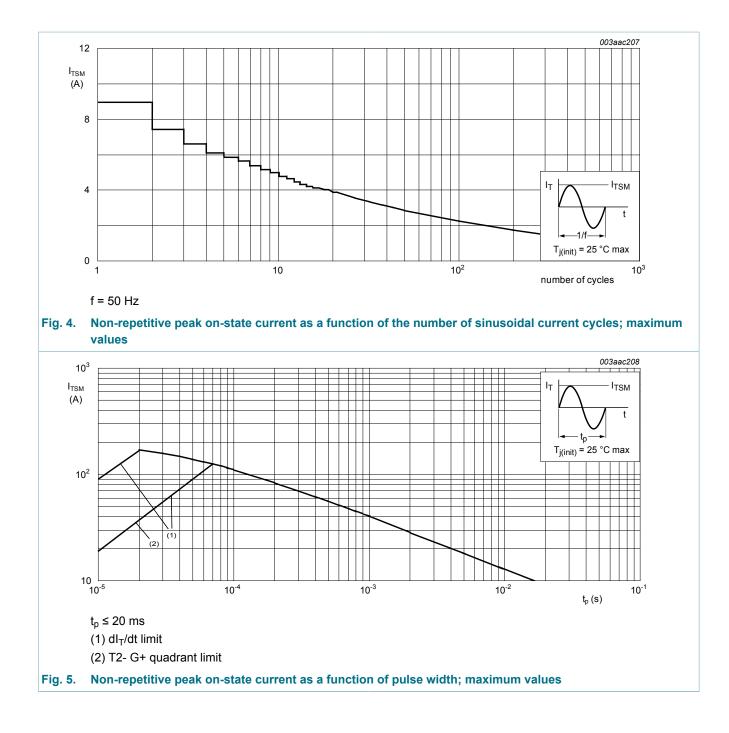
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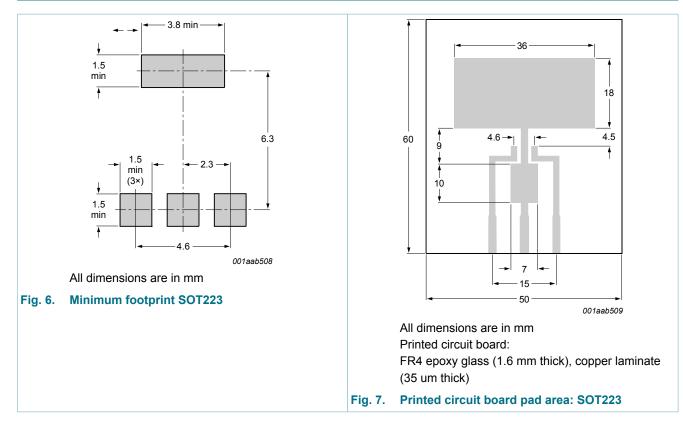
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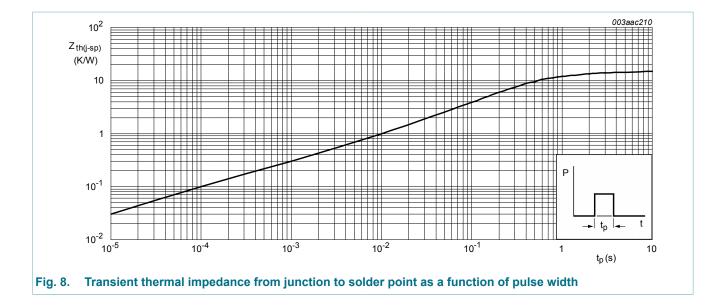
### 8. Thermal characteristics

Table 5. Th	nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	full cycle; <u>Fig. 8</u>	-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance	full cycle; for minimum footprint; Fig. 6	-	156	-	K/W
	from junction to ambient	full cycle; for pad area; Fig. 7	-	70	-	K/W



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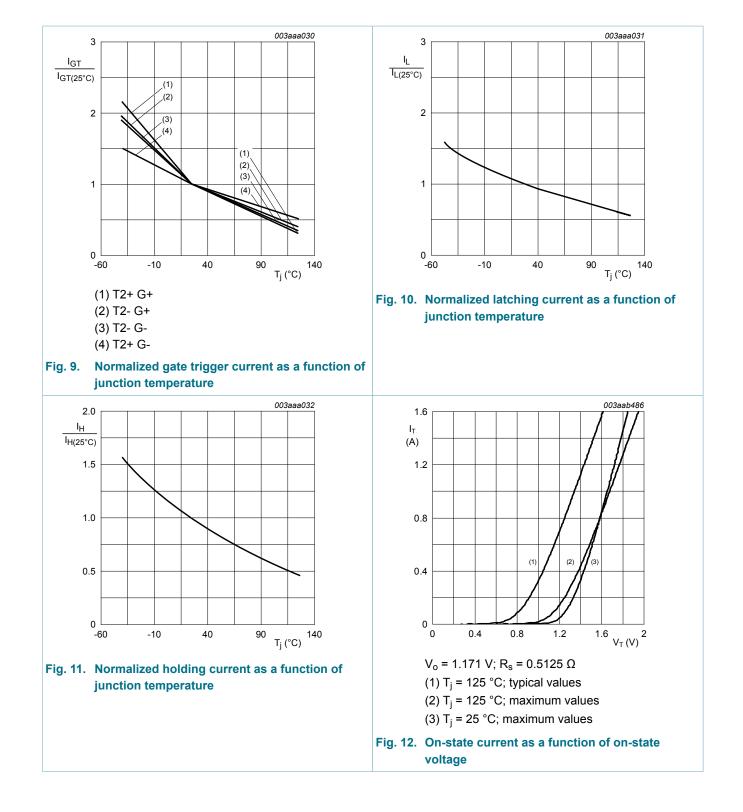
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## 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1	5	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 9}$	-	2	5	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 9}$	-	2	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	4	7	mA
ΙL	latching current	$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	5	10	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1	10	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1	10	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	2	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	1	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 0.85 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.35	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 13	-	0.9	1.5	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 110 °C; Fig. 13	0.1	0.7	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	aracteristics	· · · · · · · · · · · · · · · · · · ·				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; T <sub>j</sub> = 110 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	30	45	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 50 °C; $dI_{com}/dt$ = 0.3 A/ ms; $I_T$ = 0.84 A; gate open circuit	-	5	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 1 A; $V_D$ = 400 V; $I_G$ = 25 mA; $dI_G/dt$ = 5 A/µs	-	2	-	μs

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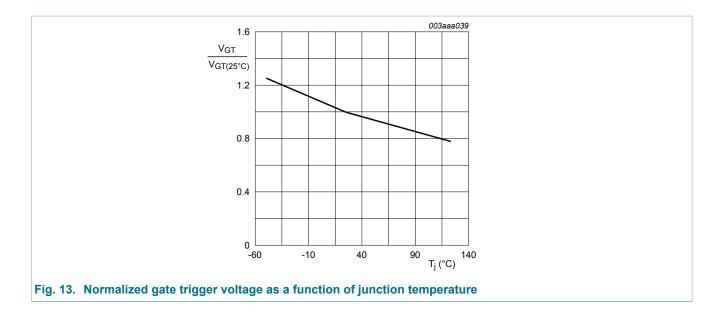


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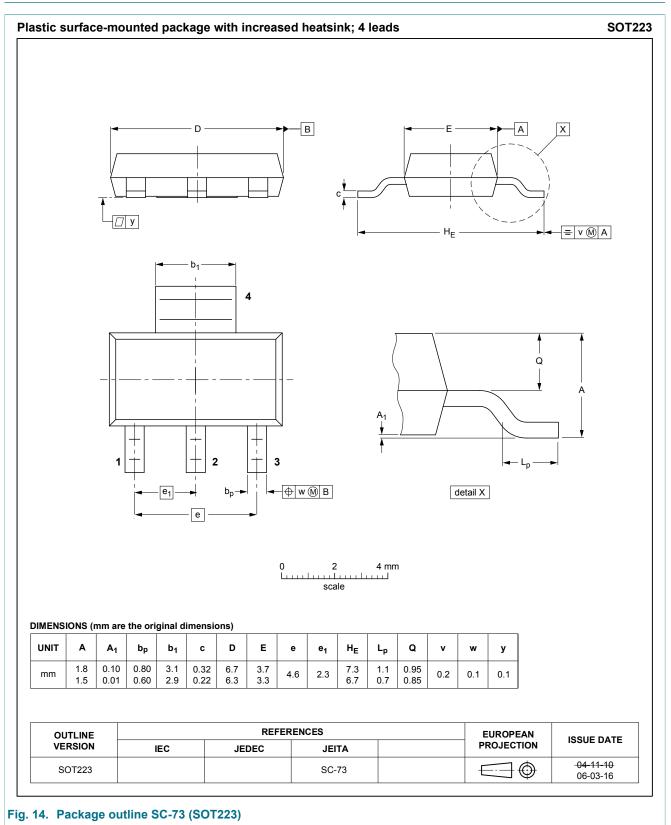
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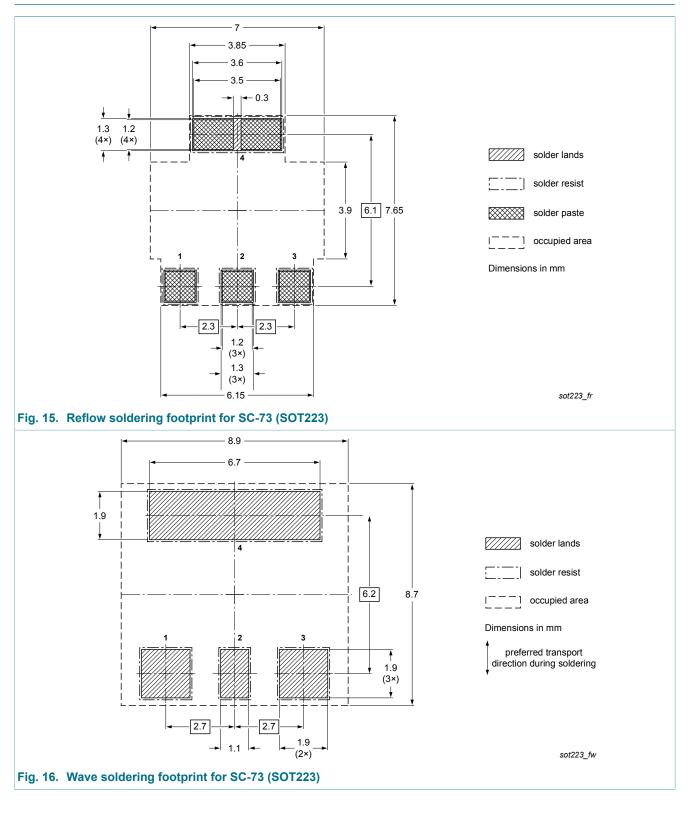
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## 10. Package outline



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### 11. Soldering



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### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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